

# EPIGAP Optronik GmbH

Koepenicker Str. 325b  
 D-12555 Berlin  
 Fon: +49 (0)30 657637 60  
 Fax: +49 (0)30 657637 70  
 sales@epigap-optronic.de



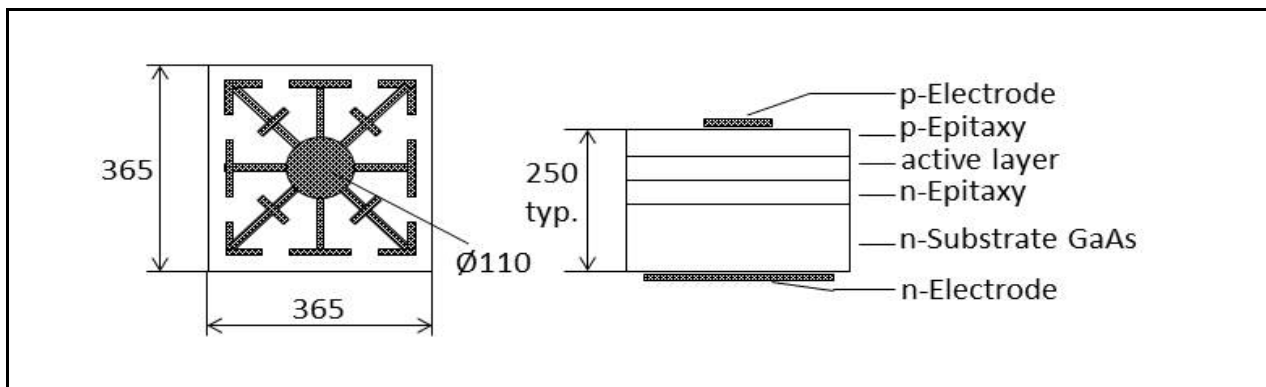
## Data Sheet

### LED Chip Infrared

EOLC-970-17D

Rev. 05, 2017

Radiation	Type	Electrodes
Infrared	MQW / GaAs	P (anode) up



### Maximum ratings

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)	$T_{amb}=25^{\circ}C$	$I_F$	100	mA
Reverse voltage		$V_R$	5	V
Storage and operating temp. range	for bare chips	$T_{amb}$	-40...+100	$^{\circ}C$
Storage temperature range	for chips on blue tape	$T_{stg}$	+5...+35	$^{\circ}C$
Junction temperature		$T_J$	+125	$^{\circ}C$

### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}C$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=20\text{ mA}$	$V_F$		1.25	1.45	V
Reverse current	$I_R=5\text{ V}$	$I_R$			10	$\mu A$
Radiant power*	$I_F=20\text{ mA}$	$\Phi_e$	1.8	2		mW
Peak wavelength	$I_F=20\text{ mA}$	$\lambda_p$		970		nm
FWHM	$I_F=20\text{ mA}$	$\lambda_{0.5}$		35		nm
Switching times	$I_F=20\text{ mA}$	$t_r, t_f$		15; 20		ns

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 007



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.